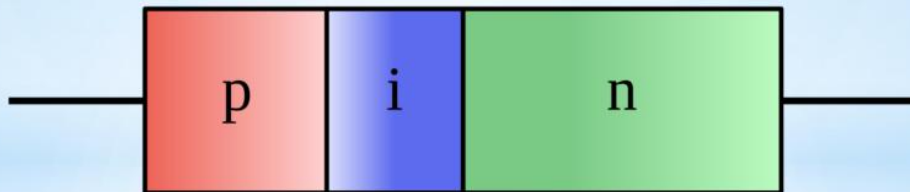




GaAs ultrafast pin-diode chips



GaAs rectifier pin-diode chip ADV 118AN5.

- Ultra-fast switching
- High radiation resistance
- High-temperature diode structures

Electrical characteristics

Parameter	Symbol	Unit	Value			Test conditions	Remark
			Min.	Typ.	Max.		
Forward voltage drop	V_F	V	-	1,4	1,5	$I_F=1A$ at $T=+25$ °C(normal cond.)	2
			-	1,6	1,7	$I_F=1A$ at $T=-60$ °C	
Reverse leakage current	I_R	uA	-	-	10	$V_R=700$ V at $T=+25$ °C(normal cond.)	1
			-	-	100	$V_R=700$ V at $T=+125$ °C	2
Breakdown voltage	V_R	V	700	900	-	$I_R=100\mu A$	1
Reverse recovery time	t_{rr}	ns	-	30	35	$di/dt=100A/ms$, $V_R=30$ V $I_F=1A$	2

Remark:
1-controlled parameter of chip diode (packageless);
2 - controlled parameter of inbuilt to the package diode

Design

Chip's size, mm	1,4 x 1,4 $\pm 0,03$ $\pm 0,03$	
Chip thickness (H), μm	380 ± 15	
Size of anode part, mm	1,4 x 1,4 $\pm 0,03$ $\pm 0,03$	
Size of cathode part, mm	0,9 x 0,9 $-0,01$ $-0,01$	
Anode metallization	Au	
Cathode metallization	Au	
Glassification junction	polyimide	